

## DESCRIPTION

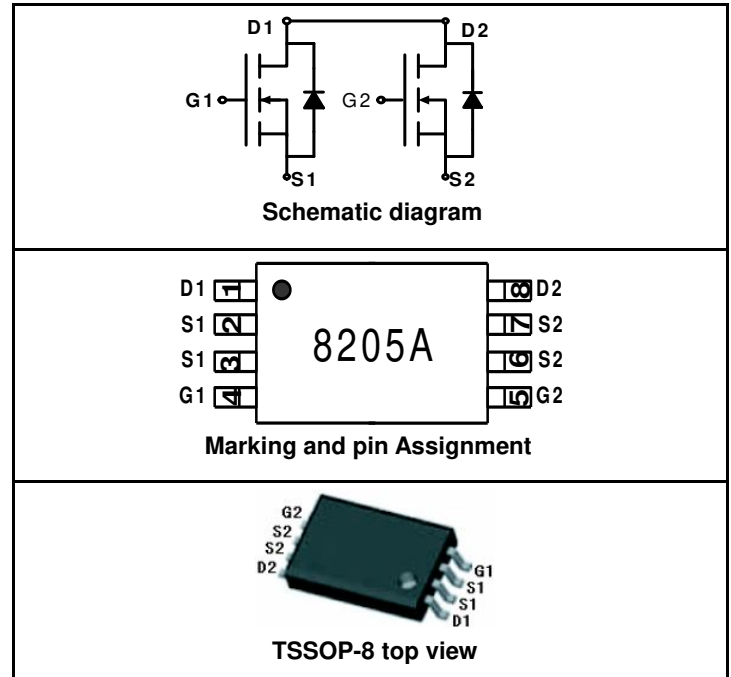
The SSF8205A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 0.65V. This device is suitable for use as a Battery protection or in other Switching application.

## GENERAL FEATURES

- $V_{DS} = 20V, I_D = 6A$   
 $R_{DS(ON)} < 37.5m\Omega @ V_{GS}=2.5V$   
 $R_{DS(ON)} < 27.5m\Omega @ V_{GS}=4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

## Application

- Battery protection
- Load switch
- Power management



## PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
8205A	SSF8205A	TSSOP-8	Ø330mm	12mm	3000 units

## ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	±10	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D$	6	A
	$I_{DM}$	25	A
Maximum Power Dissipation	$P_D$	1.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

## THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83	°C/W
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## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=18V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 10V, V_{DS}=0V$			±100	nA
<b>ON CHARACTERISTICS (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.65	1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=4.5A$		21	27.5	mΩ
		$V_{GS}=2.5V, I_D=3.5A$		30	37.5	mΩ

# SSF8205A

Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=4.5A$		10		S
<b>DYNAMIC CHARACTERISTICS (Note4)</b>						
Input Capacitance	$C_{ISS}$	$V_{DS}=8V, V_{GS}=0V,$ $F=1.0MHz$		600		PF
Output Capacitance	$C_{OSS}$			330		PF
Reverse Transfer Capacitance	$C_{RSS}$			140		PF
<b>SWITCHING CHARACTERISTICS (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$		10	20	nS
Turn-on Rise Time	$t_r$			11	25	nS
Turn-Off Delay Time	$t_{d(off)}$			35	70	nS
Turn-Off Fall Time	$t_f$			30	60	nS
Total Gate Charge	$Q_g$	$V_{DS}=10V, I_D=6A,$ $V_{GS}=4.5V$		10	15	nC
Gate-Source Charge	$Q_{gs}$			2.3		nC
Gate-Drain Charge	$Q_{gd}$			3		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=1.7A$		0.72	1.2	V
Diode Forward Current (Note 2)	$I_S$				1.7	A

## NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing.

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

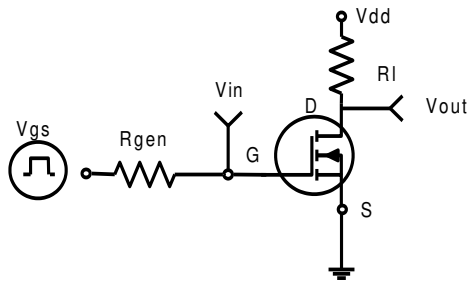


Figure 1: Switching Test Circuit

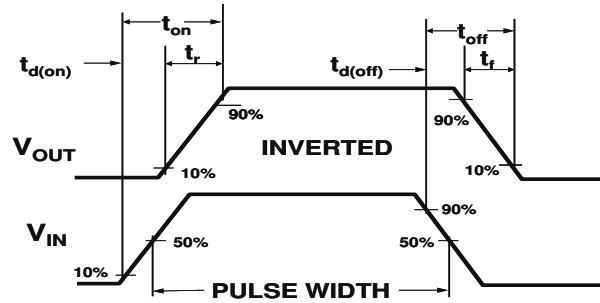


Figure 2: Switching Waveforms

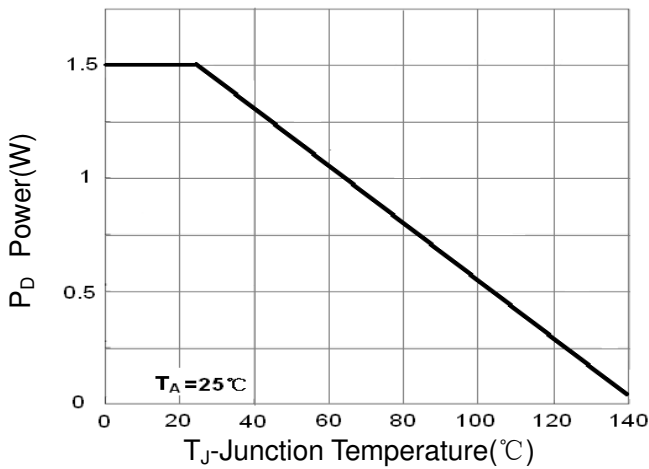


Figure 3 Power Dissipation

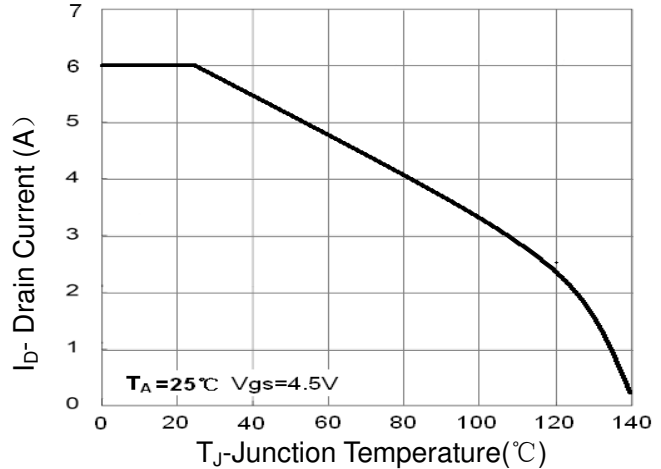


Figure 4 Drain Current

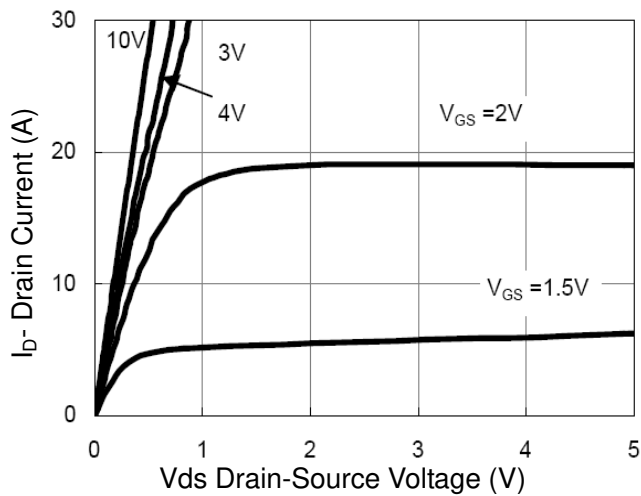


Figure 5 Output CHARACTERISTICS

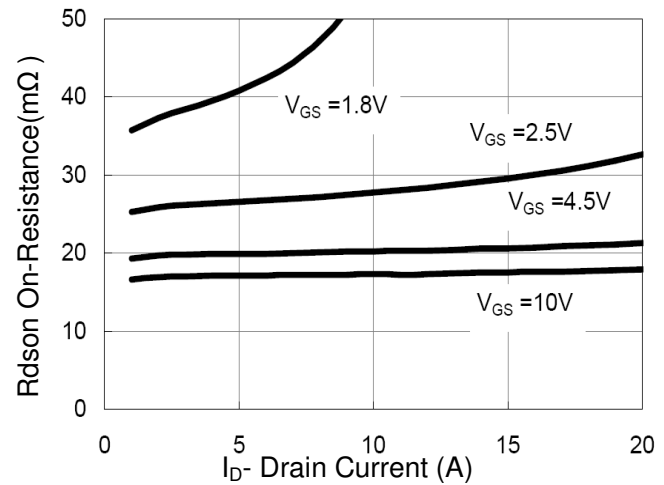
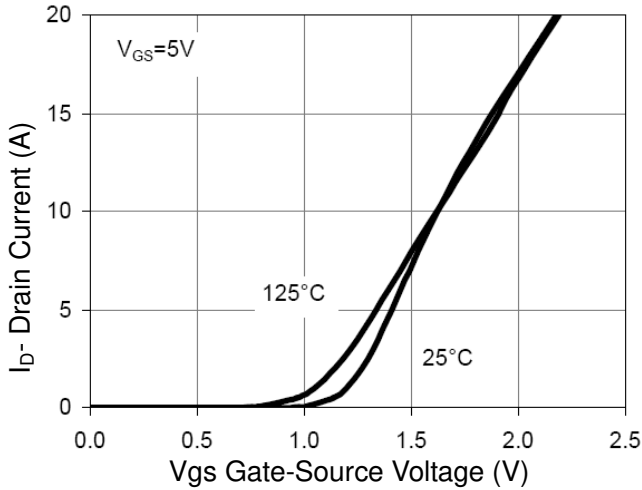
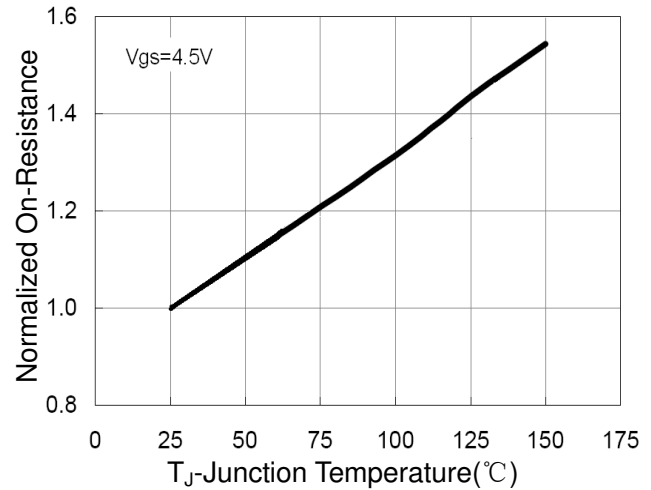


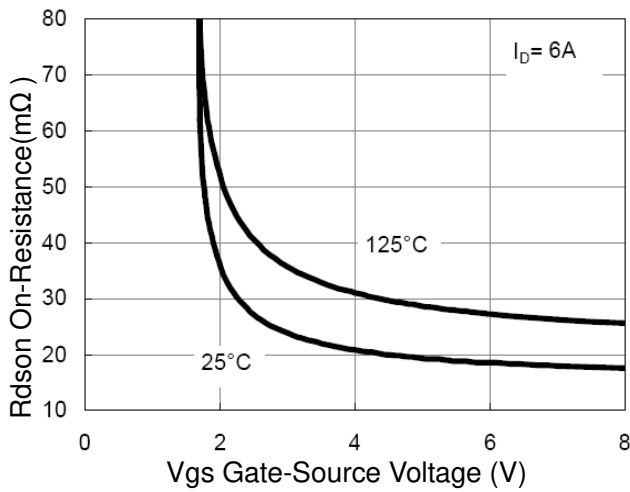
Figure 6 Drain-Source On-Resistance



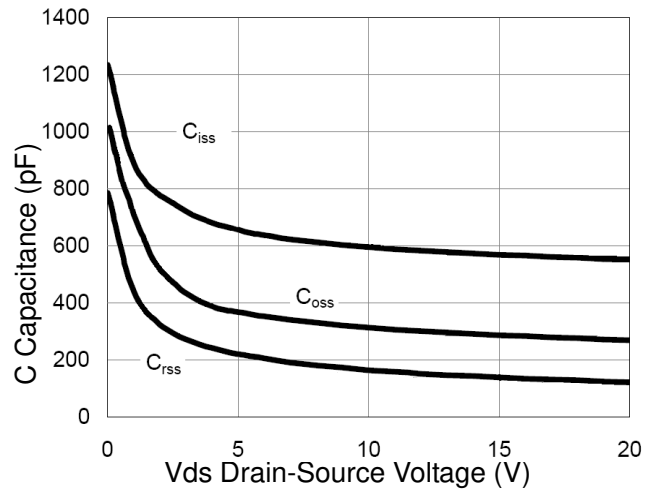
**Figure 7 Transfer Characteristics**



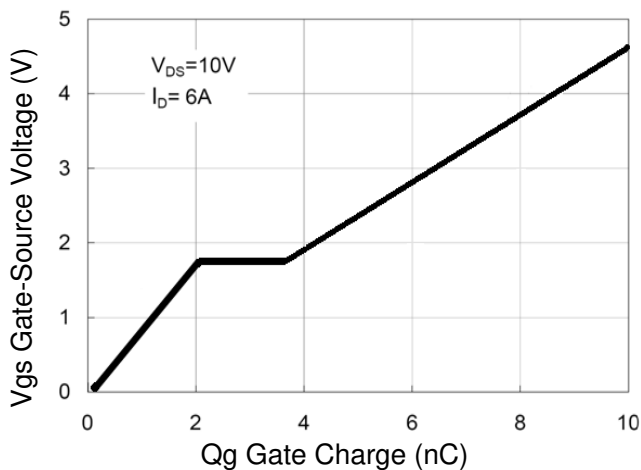
**Figure 8 Drain-Source On-Resistance**



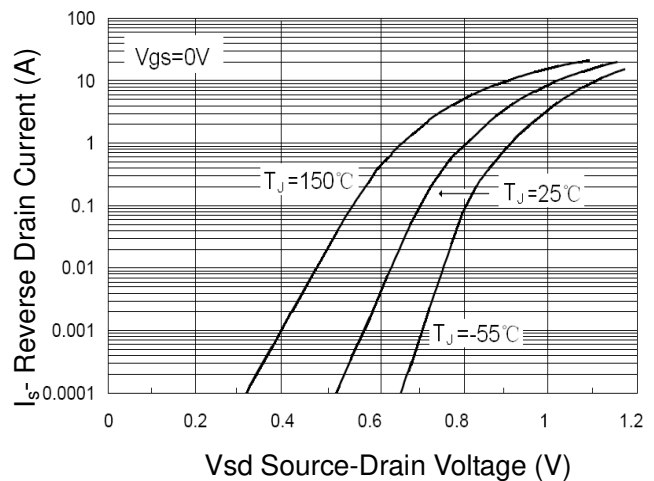
**Figure 9 Rdson vs Vgs**



**Figure 10 Capacitance vs Vds**



**Figure 11 Gate Charge**



**Figure 12 Source- Drain Diode Forward**

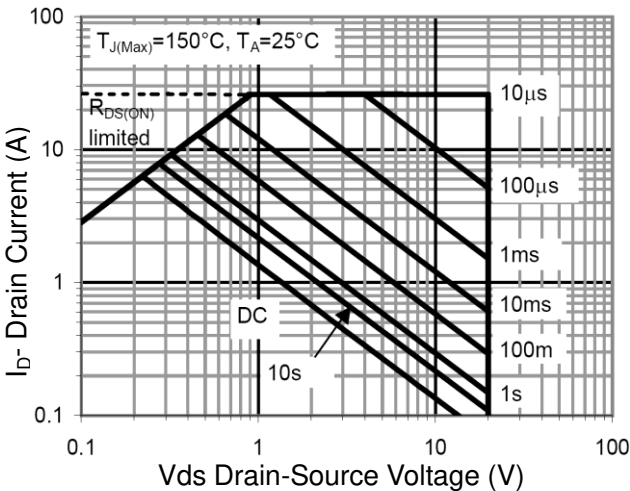


Figure 13 Safe Operation Area

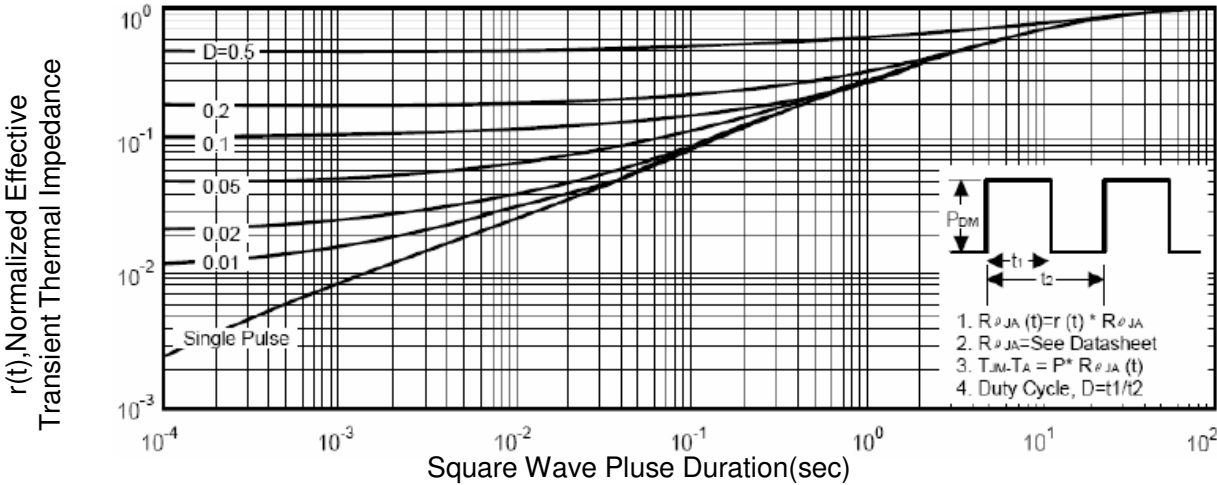
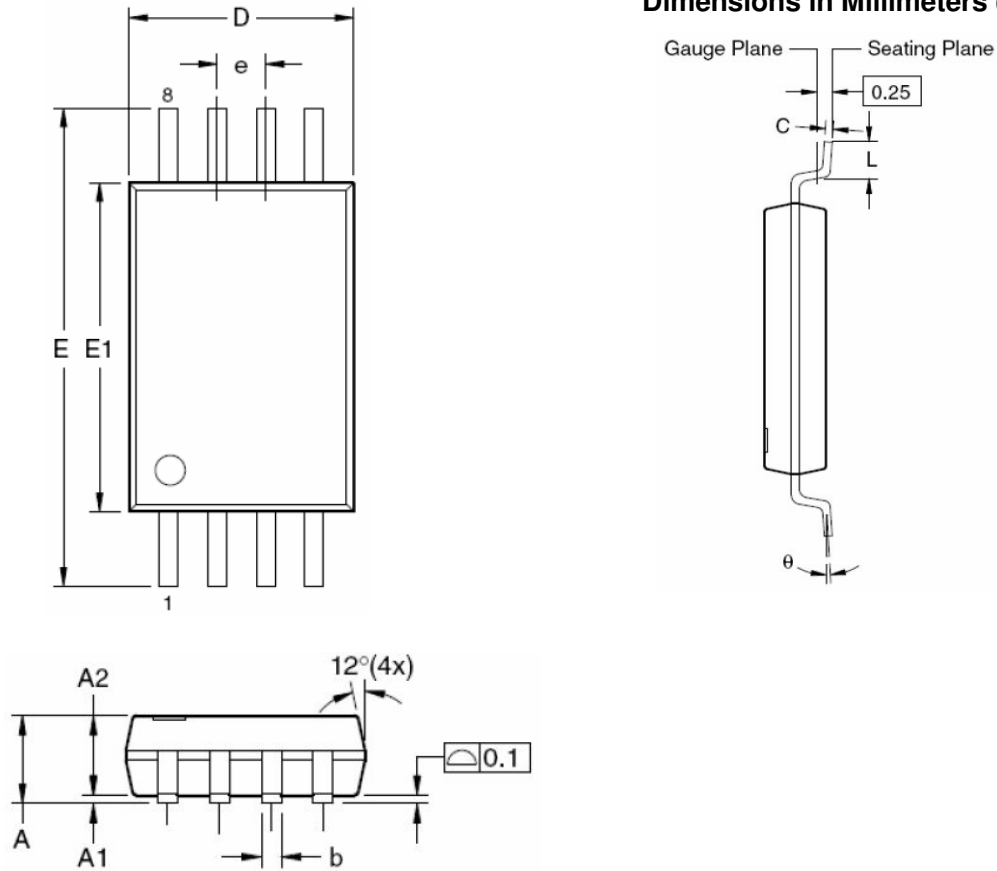


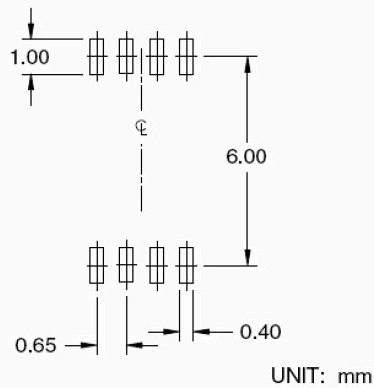
Figure 14 Normalized Maximum Transient Thermal Impedance

## TSSOP-8 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)



### RECOMMENDED LAND PATTERN



### Dimensions in millimeters

Symbols	Min.	Nom.	Max.
A	—	—	1.20
A1	0.05	—	0.15
A2	0.80	1.00	1.05
b	0.19	—	0.30
C	0.09	—	0.20
D	2.90	3.00	3.10
E	6.40 BSC		
E1	4.30	4.40	4.50
e	0.65 BSC		
L	0.45	0.60	0.75
θ	0°	—	8°

### Dimensions in inches

Symbols	Min.	Nom.	Max.
A	—	—	0.047
A1	0.002	—	0.006
A2	0.031	0.039	0.041
b	0.007	—	0.012
C	0.004	—	0.008
D	0.114	0.118	0.122
E	0.252 BSC		
E1	0.169	0.173	0.177
e	0.026 BSC		
L	0.018	0.024	0.030
θ	0°	—	8°

### NOTES:

1. All dimensions are in millimeters.
2. Dimensions are inclusive of plating
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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